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(54) Title: METHOD FOR FORMING HIGH DENSITY PATTERNS

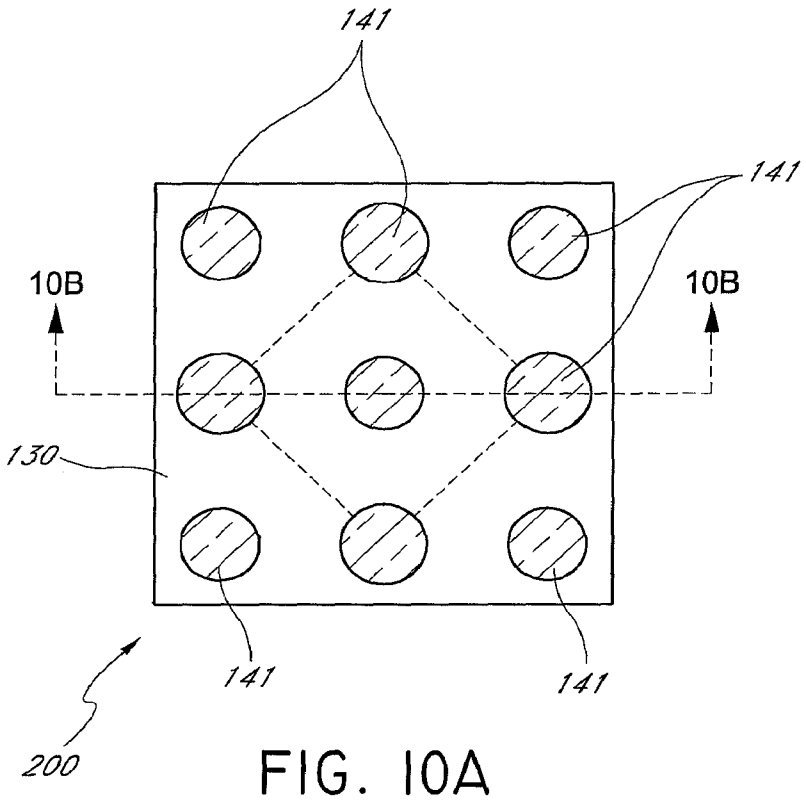


FIG. 10A

(57) Abstract: Methods are disclosed, such as those involving increasing the density of isolated features in an integrated circuit (200). In one or more embodiments, a method is provided for forming an integrated circuit (200) with a pattern of isolated features having a final density of isolated features that is greater than a starting density of isolated features in the integrated circuit (200) by a multiple of two or more. The method can include forming a pattern of pillars (122) having a density X, and forming a pattern of holes (140) amongst the pillars (122), the holes (140) having a density at least X. The pillars (122) can be selectively removed to form a pattern of holes (141) having a density at least 2X. In some embodiments, plugs (150) can be formed in the pattern of holes (141). such as by epitaxial deposition on the substrate (300). in order to provide a pattern of pillars having a density 2X. In other embodiments, the pattern of holes (141) can be transferred to the substrate (100) by etching.

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